

2SC5628

Silicon NPN Epitaxial
High Frequency Amplifier / Oscillator

HITACHI

ADE-208-979A (Z)

2nd. Edition

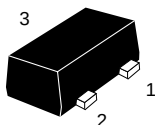
April 2001

Features

- Super compact package;
($1.4 \times 0.8 \times 0.59\text{mm}$)
- High power gain and low noise figure;
(PG = 9 dB, NF = 1.1 dB typ, at $f = 900\text{ Mhz}$, $V_{CE} = 1\text{ V}$)

Outline

MFPK



1. Emitter
2. Base
3. Collector

Note: Marking is "XZ-".

Absolute Maximum Ratings (Ta = 25°C)

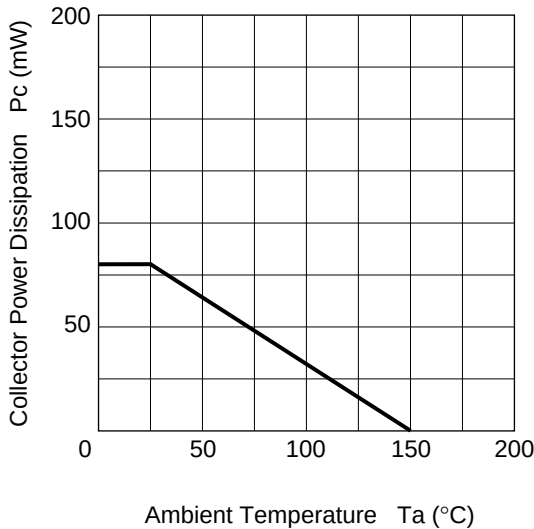
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	15	V
Collector to emitter voltage	V _{CEO}	8	V
Emitter to base voltage	V _{EBO}	1.5	V
Collector current	I _C	50	mA
Collector power dissipation	Pc	80	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

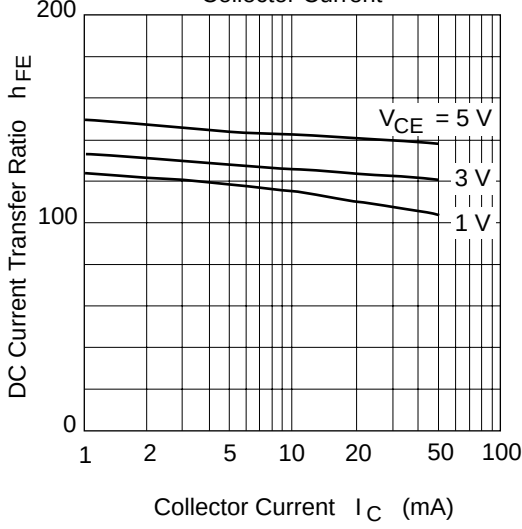
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	V _{(BR)CBO}	15	—	—	V	I _C = 10μA , I _E = 0
Collector cutoff current	I _{CBO}	—	—	1	μA	V _{CB} = 12V , I _E = 0
Collector cutoff current	I _{CEO}	—	—	1	mA	V _{CE} = 8V , R _{BE} = ∞
Emitter cutoff current	I _{EBO}	—	—	10	μA	V _{EB} = 1.5V , I _C = 0
DC current transfer ratio	h _{FE}	50	100	160	V	V _{CE} = 1V , I _C = 5mA
Collector output capacitance	Cob	—	0.55	0.85	pF	V _{CB} = 1V , I _E = 0 f = 1MHz
Gain bandwidth product	f _T	6	9	—	GHz	V _{CE} = 1V , I _C = 5mA
Power gain	PG	11	14	—	dB	V _{CE} = 1V , I _C = 5mA f = 900MHz
Noise figure	NF	—	1.1	2.0	dB	V _{CE} = 1V , I _C = 5mA f = 900MHz

Main Characteristics

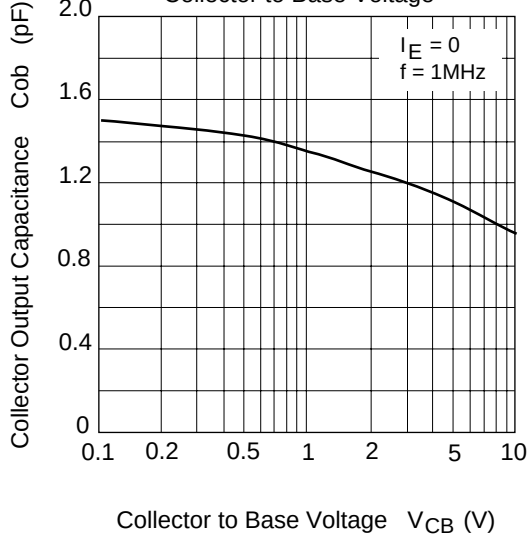
Maximum Collector Dissipation Curve



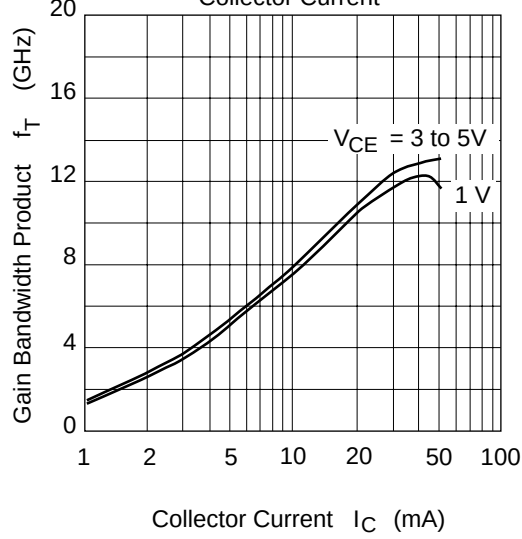
DC Current Transfer Ratio vs. Collector Current

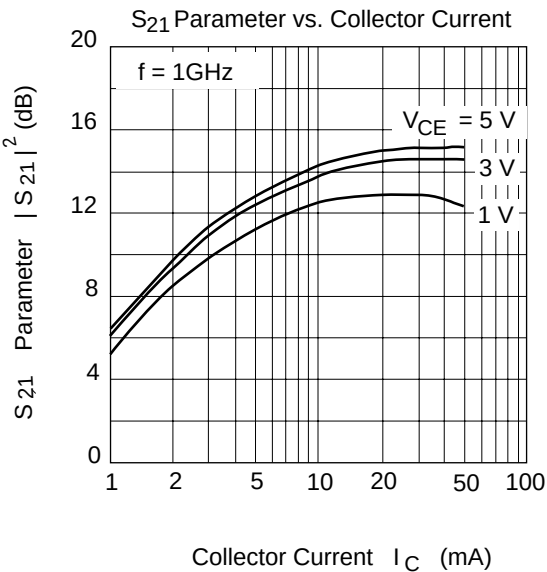
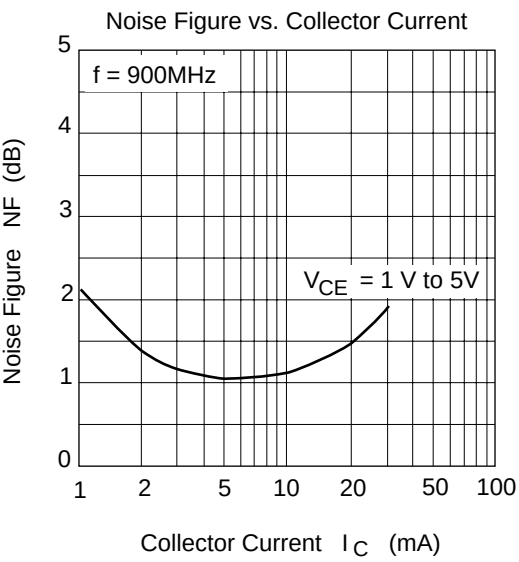
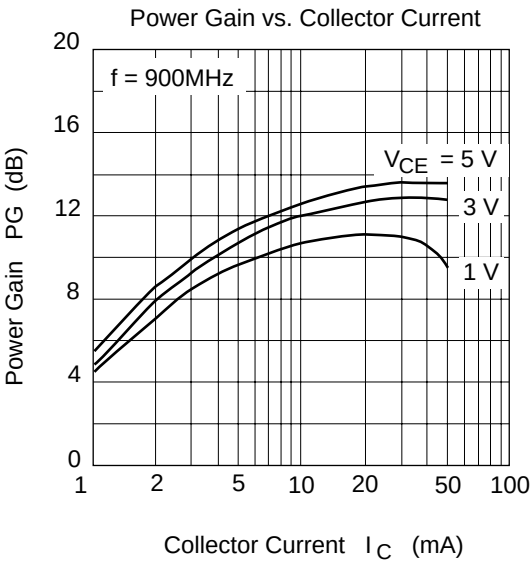


Collector Output Capacitance vs. Collector to Base Voltage

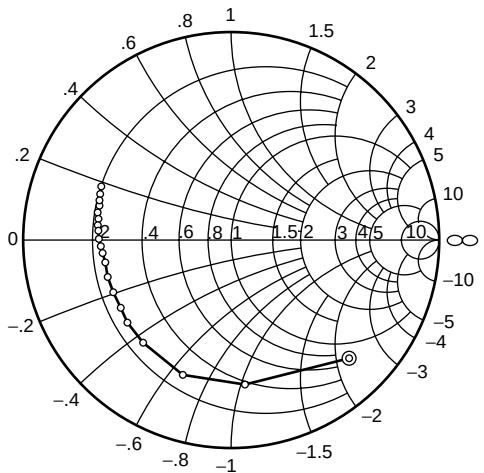


Gain Bandwidth Product vs. Collector Current





S11 Parameter vs. Frequency

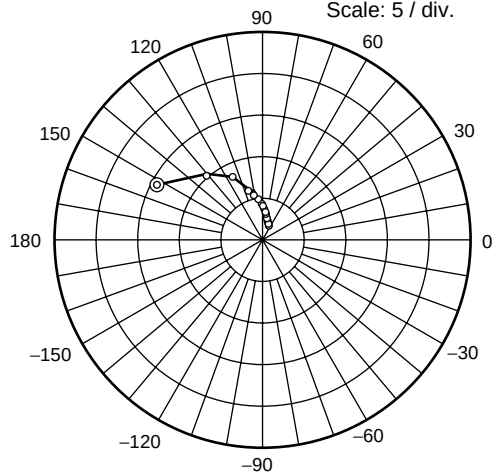


Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S21 Parameter vs. Frequency

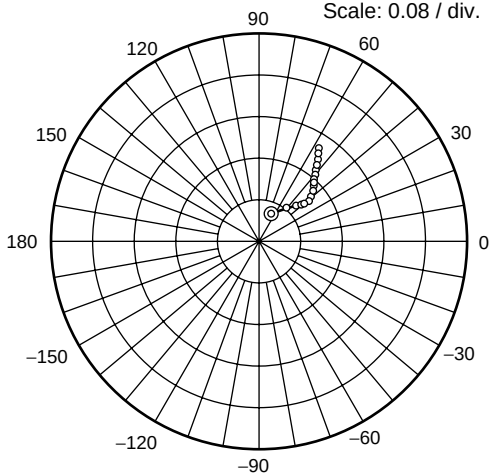


Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S12 Parameter vs. Frequency

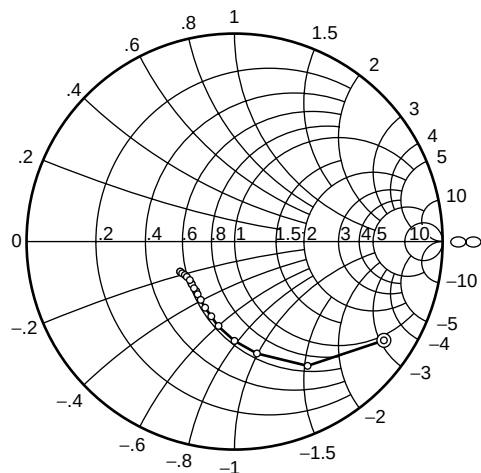


Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S22 Parameter vs. Frequency

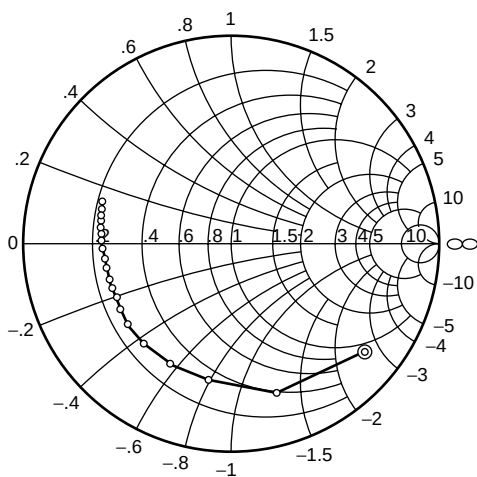


Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)

⊙—○

S11 Parameter vs. Frequency

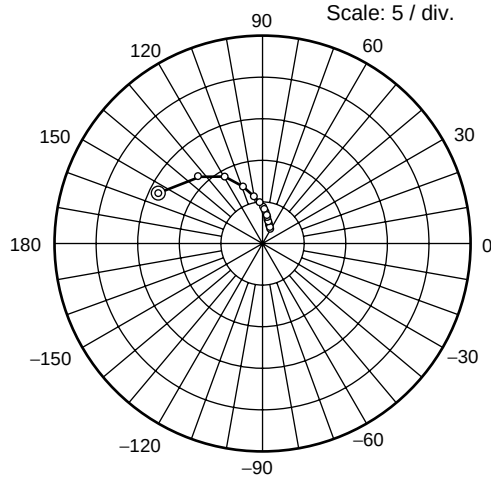


Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S21 Parameter vs. Frequency

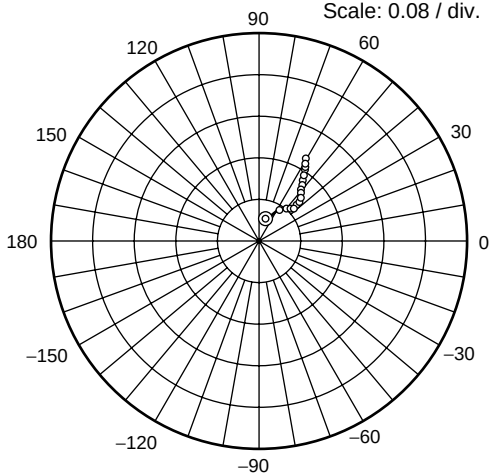


Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S12 Parameter vs. Frequency

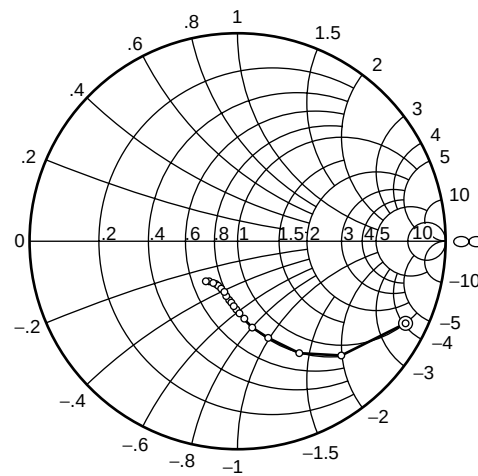


Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S22 Parameter vs. Frequency



Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



Sparameter ($V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$, $Z_o = 50\ \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.815	−46.1	13.63	152.2	0.0509	67.0	0.882	−32.5
200	0.734	−84.6	10.68	130.6	0.0834	51.0	0.695	−58.5
300	0.692	−111.2	8.23	116.8	0.0998	42.9	0.550	−76.0
400	0.665	−127.4	6.58	107.9	0.108	39.5	0.459	−88.5
500	0.650	−139.6	5.44	101.4	0.114	38.0	0.399	−98.1
600	0.644	−148.8	4.61	96.3	0.120	38.3	0.360	−105.7
700	0.640	−155.6	4.03	92.2	0.124	39.0	0.333	−112.2
800	0.641	−161.6	3.56	88.6	0.128	39.9	0.315	−117.8
900	0.638	−166.9	3.20	85.3	0.134	41.8	0.301	−122.4
1000	0.638	−171.6	2.90	82.2	0.138	43.5	0.292	−126.7
1100	0.643	−175.1	2.66	79.6	0.143	44.4	0.286	−130.2
1200	0.643	−178.5	2.46	77.2	0.149	46.2	0.280	−133.6
1300	0.648	178.5	2.28	74.9	0.154	47.8	0.279	−135.6
1400	0.651	175.4	2.15	72.8	0.161	49.1	0.278	−138.6
1500	0.658	173.2	2.03	70.5	0.168	50.9	0.277	−140.9
1600	0.663	170.0	1.92	68.5	0.174	51.8	0.279	−143.3
1700	0.667	167.2	1.82	66.7	0.182	53.2	0.281	−145.0
1800	0.669	165.0	1.74	64.4	0.189	54.6	0.282	−147.1
1900	0.673	163.1	1.67	63.2	0.196	55.5	0.286	−149.3
2000	0.682	161.0	1.60	61.4	0.204	56.4	0.289	−150.6

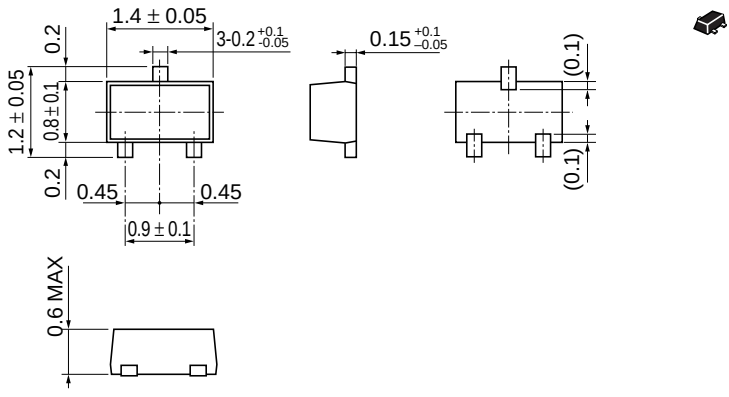
2SC5628

Sparameter (V_{CE} = 3 V, I_C = 5 mA, Z_o = 50 Ω)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.826	−39.3	14.04	155.5	0.0412	69.9	0.906	−25.8
200	0.746	−74.6	11.47	134.9	0.0700	54.9	0.738	−47.3
300	0.685	−100.5	9.14	121.1	0.0864	46.7	0.591	−61.9
400	0.646	−117.4	7.41	111.9	0.0950	43.0	0.490	−71.9
500	0.627	−130.7	6.19	104.8	0.101	41.3	0.419	−79.9
600	0.617	−141.0	5.27	99.6	0.107	41.3	0.369	−85.7
700	0.606	−149.0	4.61	95.0	0.111	41.6	0.333	−90.7
800	0.598	−155.4	4.09	91.6	0.115	42.5	0.307	−95.3
900	0.605	−161.3	3.67	87.7	0.120	44.3	0.287	−99.0
1000	0.604	−166.1	3.35	84.7	0.124	45.6	0.273	−102.6
1100	0.604	−170.6	3.06	81.8	0.129	46.8	0.262	−106.0
1200	0.607	−174.2	2.83	79.5	0.134	49.0	0.253	−108.8
1300	0.605	−178.2	2.62	77.1	0.139	50.4	0.249	−111.0
1400	0.608	178.9	2.47	74.9	0.145	51.9	0.245	−114.3
1500	0.618	175.5	2.32	72.7	0.152	53.4	0.242	−116.6
1600	0.622	172.4	2.19	70.7	0.157	54.8	0.241	−118.9
1700	0.627	170.0	2.08	68.9	0.164	56.2	0.241	−121.3
1800	0.629	166.9	1.99	66.7	0.171	57.6	0.242	−123.4
1900	0.633	164.3	1.90	65.2	0.177	58.7	0.243	−125.9
2000	0.641	162.3	1.82	63.4	0.186	59.5	0.245	−127.7

Package Dimensions

Unit: mm



Hitachi Code	MFPAK
JEDEC	—
EIAJ	—
Mass (reference value)	0.0016 g

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